AT0P6SN030EQSB-Q1

N-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	420mΩ@4.5V	0.6A
	540mΩ@2.5V	

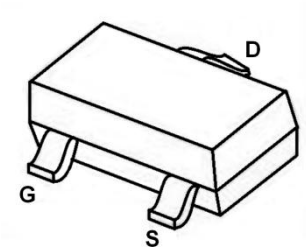
Feature

- N-Channel switch with low RDS(on)
- Operated at low logic level gate drive
- Suffix “-Q1” for AEC-Q101

Application

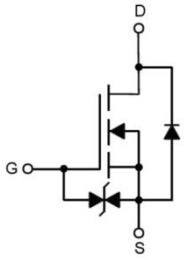
- Load switch appliances

Package

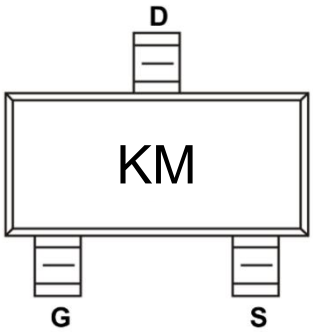


SOT-323

Circuit diagram



Marking



Absolute maximum ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current[1)]	I_D	0.6	A
Pulsed Drain Current (t_p =10μs)	I_{DM}	1.8	A
Single Pulse Avalanche Energy[2)]	E_{AS}	2	mJ
Power Dissipation[1)]	P_D	0.2	W
Thermal Resistance Junction to Ambient[1)]	$R_{\theta JA}$	625	℃/W
Operating Junction Temperature	T_J	-55 ~ +150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =250μA	30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =30V, V_{GS} =0V			1	μA
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±10V			±3	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5	0.95	1.5	V
Drain-source on-resistance[3)]	$R_{DS(on)}$	V_{GS} =4.5V, I_D =0.6A		335	420	mΩ
		V_{GS} =2.5V, I_D =0.3A		404	540	
Dynamic characteristics[4)]						
Input Capacitance	C_{iss}	V_{DS} =10V, V_{GS} =0V, f =1MHz		73		pF
Output Capacitance	C_{oss}			29		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge	Q_g	V_{DS} =15V, V_{GS} =4.5V, I_D =0.8A		2.23		nC
Gate-Source Charge	Q_{gs}			0.63		
Gate-Drain Charge	Q_{gd}			0.38		
Turn-on delay time	$t_{d(on)}$	V_{DS} =15V, V_{GS} =4.5V, I_D =0.7A R_G =51Ω		5		nS
Turn-on rise time	t_r			8.2		
Turn-off delay time	$t_{d(off)}$			23		
Turn-off fall time	t_f			41		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				0.6	A
Diode Forward voltage[3)]	V_{SD}	V_{GS} =0V, I_S =0.6A			1.2	V

Notes:

1) The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2) The EAS data shows Max. rating. The test condition is V_{DD} =15V, V_{GS} =6V, L =10mH.

3) The data tested by pulsed, pulse width ≤300μs, duty cycle ≤2%.

4) Guaranteed by design, not subject to production testing.

Typical Characteristics

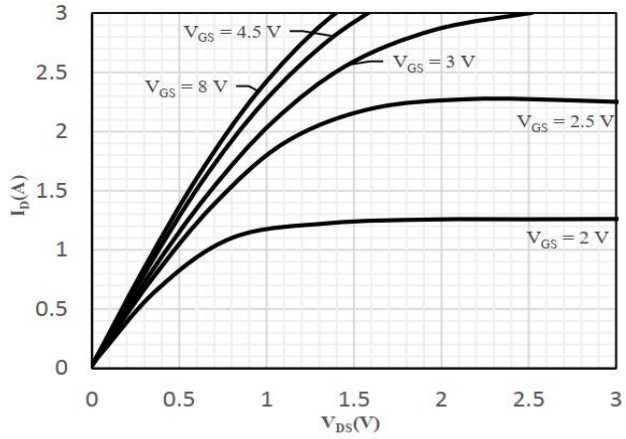


Fig 1 Output Characteristics

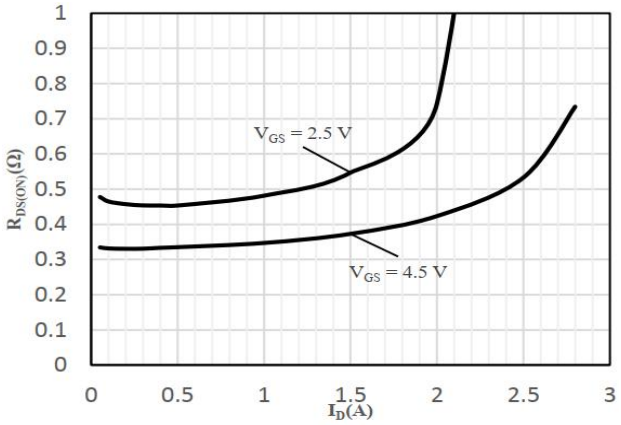


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

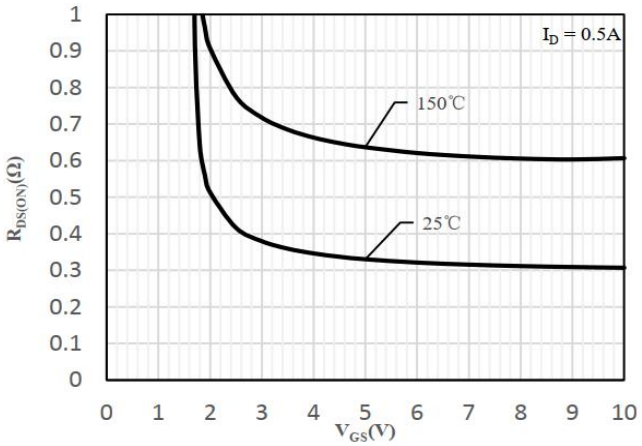


Fig 3 On-Resistance vs. Gate-Source Voltage

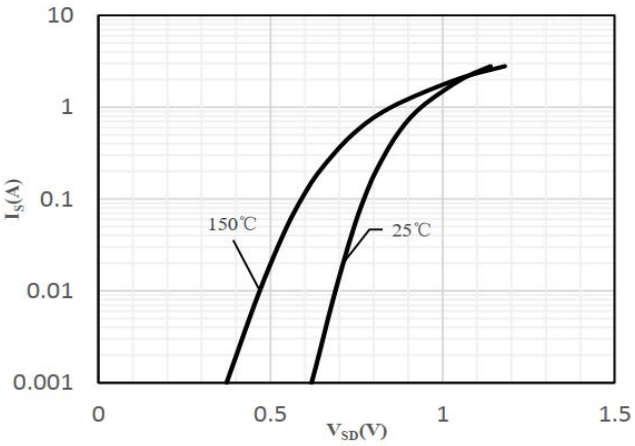


Fig 4 Body-Diode Characteristics

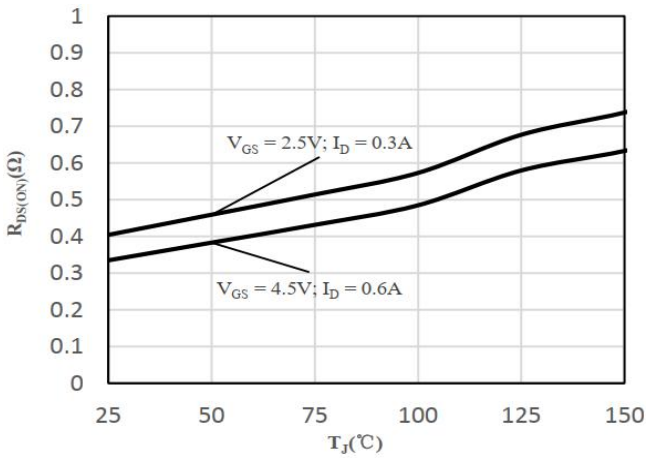


Fig 5 On-Resistance vs. Junction Temperature

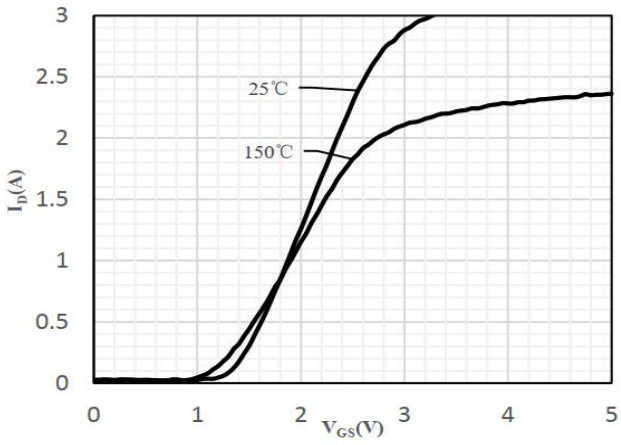


Fig 6 Transfer Characteristics

Typical Characteristics

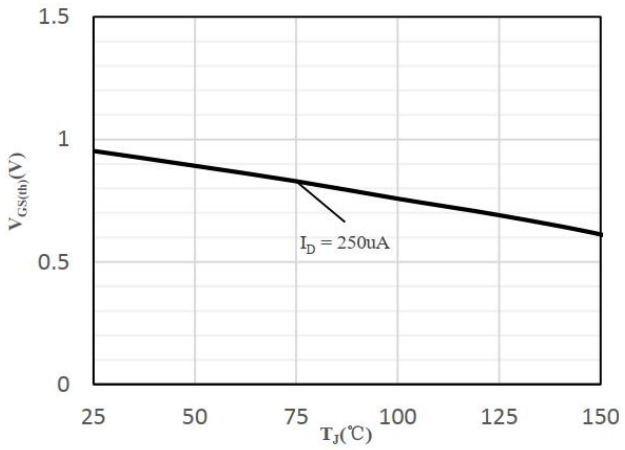


Fig 7 $V_{GS(th)}$ vs. Junction Temperature

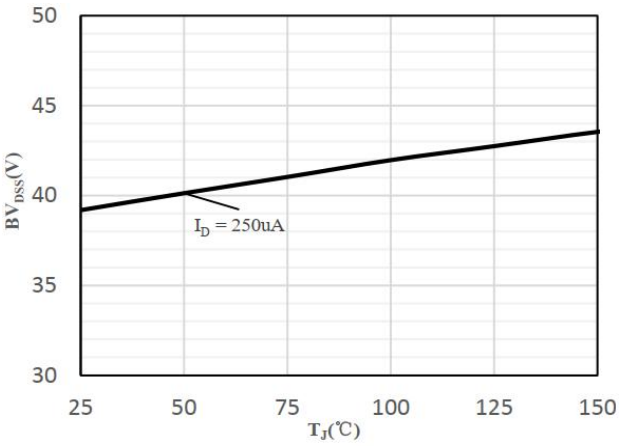


Fig 8 Breakdown Voltage vs. Junction Temperature

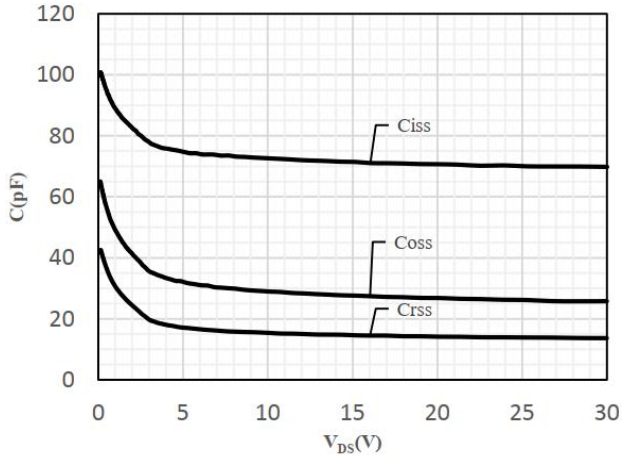


Fig 9 Capacitance Characteristics

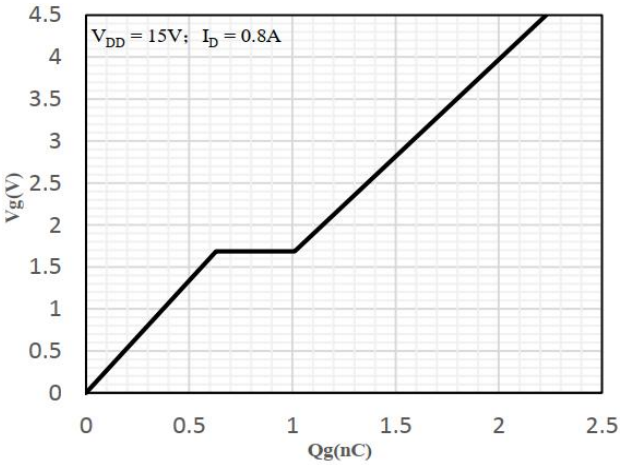
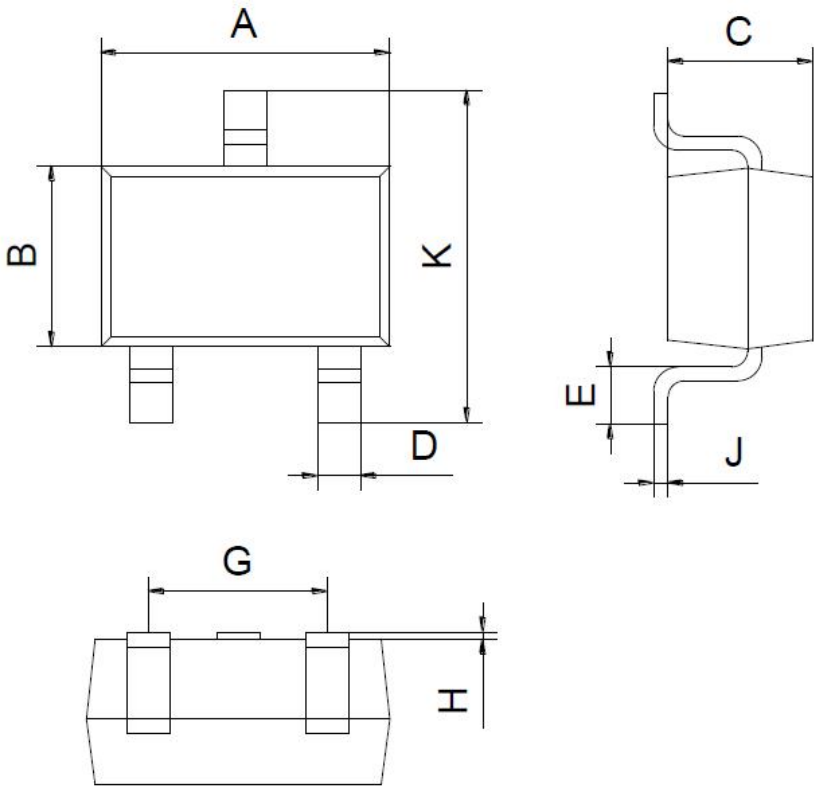


Fig 10 Gate-Charge Characteristics

SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.000	2.200	0.079	0.087
B	1.150	1.350	0.045	0.053
C	0.900	1.100	0.035	0.043
D	0.150	0.350	0.006	0.014
E	0.250	0.400	0.010	0.016
G	1.200	1.400	0.047	0.055
H	0.020	0.100	0.001	0.004
J	0.050	0.150	0.002	0.006
K	2.200	2.400	0.087	0.094